

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: HWANG ET AL.

SERIAL NO.: 10/022,349

FILED: December 20, 2001

JUN 03 2003

FOR: A SINGLE-CHIP STRUCTURE OF SILICON  
GERMANIUM PHOTODETECTOR AND HIGH-  
SPEED TRANSISTOR

GROUP ART UNIT: 2814

EXAMINER: D. WILLIE

ATTY. REFERENCE: HWAN3013/EM

TECHNOLOGY CENTER 2800

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JUN -4 2003

COMMISSIONER OF PATENTS  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Transmitted herewith is a communication/amendment in the above-identified application.

- Small entity status under 37 CFR 1.9 and 1.27 is claimed.  
 No additional fee is required.

The fee, if any, has been calculated as shown below:

Fee Basis	Number of Claims After Amendment	Highest Number Previously Paid For	Extra Claims	Small Entity	Full Fee
Total Claims	20	- 20 <sup>1</sup>	= 0 <sup>3</sup>	× \$ 9 =	× \$ 18 = \$0.00
Independent Claims	2	- 3 <sup>2</sup>	= 0 <sup>3</sup>	× \$ 42 =	× \$ 84 = \$0.00
<input type="checkbox"/> First Presentation of Proper Multiple Dependent Claim			+ \$140 =	+ \$280 =	
			TOTAL		\$0.00

<sup>1</sup> If less than 20 enter 20.<sup>2</sup> If less than 3 enter 3.<sup>3</sup> If less than 0 enter 0.

- Please charge my Deposit Account Number 02-0200 in the amount of \$\_\_\_\_\_ . A duplicate copy of this sheet is attached.
- A check in the amount of \$\_\_\_\_\_ is attached.
- The Commissioner is hereby authorized to charge any additional fees associated with this communication, including fees due under 37 CFR 1.16 and 37 CFR 1.17 or credit any overpayment to Deposit Account Number 02-0200. A duplicate copy of this sheet is attached.
- Also enclosed is/are:

BACON & THOMAS, PLLC  
625 SLATERS LANE - FOURTH FLOOR  
ALEXANDRIA, VIRGINIA 22314-1176  
(703) 683-0500

23364

PATENT TRADEMARK OFFICE

DATE: June 3, 2003

Respectfully submitted,

Richard E. Fichter  
Attorney for Applicant  
Registration Number: 26,382

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



Please Application of:

HWANG et al.

Serial No.: 10/022,349

Filed: December 20, 2001

For: A SINGLE-CHIP STRUCTURE OF SILICON GERMANIUM PHOTODETECTOR AND HIGH-SPEED TRANSISTOR

Group Art Unit: 2814

Examiner: D. Wille

#7/C  
marsh  
6/6/03

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AMENDMENT

Assistant Commissioner for Patents  
Washington, D.C. 20231

Sir:

This is in response to the Official Action of March 3, 2003, in connection with the above-identified application.

Please amend the above-identified application as follows.

IN THE CLAIMS:

Please add the following new claims to the application.

37(New). A single-chip structure of silicon germanium photodetectors and high-speed transistors according to claim 20 wherein the insulation layer is perpendicular to and touches the substrate and goes through the base layer, photo-absorbing and collector layers.

38(New). A single-chip structure of silicon germanium photodetectors and high-speed transistors according to claim 29 wherein the insulation layer is perpendicular to and touches the substrate and goes through the base layer, photo-absorbing and collector layers.